

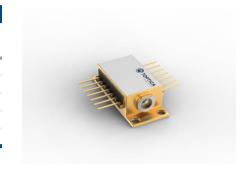
2024-05-03

SINGLE FREQUENCY LASER **DFB Laser**



O	Dona day	4 14	
Genera	Produ	ct ini	formation

Product	Application
795 nm DFB Laser	Spectroscopy (Rb D1 line)
with hermetic 14-Pin Butterfly Housing (RoHS compliant)	Metrology
including Monitor Diode, Thermoelectric Cooler and Thermistor	
with integrated μ-Isolator and Beam Collimation	



Absolute Maximum Ratings

Parameter	Symbol	Unit	min	typ	max
Storage Temperature	Ts	° C	-40		85
Operational Temperature at Case	T_C	° C	-40		85
Operational Temperature at Chip	T_{chip}	° C	5		50
Forward Current	I _F	mA			170
Reverse Voltage	V_{R}	V			2
Output Power	P_{opt}	mW			45
TEC Current	I _{TEC}	Α			1,4
TEC Voltage	V_{TEC}	V			4,8

Measurement Conditions / Comments

Stress in excess of one of the Absolute Maximum Ratings may damage the laser. Please note that a damaging optical power level may occur although the maximum current is not reached. These are stress ratings only, and functional operation at these or any other conditions beyond those indicated under Recommended Operational Conditions is not implied.

Recommended Operational Conditions

Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T _{case}	°C	-20		60
Operational Temperature at Chip	T_{chip}	° C	10		45
Forward Current	I _F	mA			160
Output Power	P_{opt}	mW	10		40

Measurement Conditions / Comments
measured by integrated Thermistor

Tchip = 25° at BOL Characteristics

$\begin{array}{cccccccccccccccccccccccccccccccccccc$	796
Target Wavelength λ_T nm 794.5	
	8
Linewidth $\Delta\lambda$ MHz 0,6	1
Mode-hop free Tuning Range $$\Delta\lambda_{tune}$$ pm $~25$	
Sidemode Suppression Ratio SMSR dB 30 45	
Temp. Coefficient of Wavelength $d\lambda / dT$ nm/K 0,06	
Current Coefficient of Wavelength $d\lambda$ / dl nm/mA 0,00	3



Revision 0.92

2024-05-03

SINGLE FREQUENCY LASER DFB Laser



Characteristics	Tchip = 25° at BO	L			
Parameter	Symbol	Unit	min	typ	max
Mode-hop free Temperature Range	T _{chip}	° C	0		0
Laser Current	I _{LD}	mA			160
Slope Efficiency	η	mW/mA		0,4	
Threshold Current	I _{th}	mA			70
Divergence parallel	Θ	0		0,1	
Divergence perpendicular	Θ_{\perp}	0		0,1	
Beam Diameter horizontal	d	mm		1	1,2
Beam Diameter vertical	d_{\bot}	mm		0,8	1,2
Degree of Polarization	DOP	%		99	

Measurement Conditions / Comments	
Popt = 40 mW	
parallel to the base plate of the housing	
perpendicular to base plate of the housing	
parallel to the base plate of the housing	
perpendicular to base plate of the housing	
Popt = 40 mW; slant polarization (45°)	

Monitor Diode				
Parameter	Symbol Unit	min	typ	max
Monitor Detector Responsivity	I _{mon} / P _{of} μA/mW	/ 1		20

5 V	Measurement Conditions / Comments
J V	5 V

Thermoelectric Cooler					
Parameter	Symbol	Unit	min	typ	max
Current	I _{TEC}	Α		0,4	
Voltage	U_TEC	V		1,3	
Power Dissipation (total loss at case)	P _{loss}	W		0,4	
Temperature Difference	ΔΤ	K			50

Measurement Conditions / Comments			
Popt = 40 mW, ΔT = 20 K			
Popt = 40 mW, ΔT = 20 K			
Popt = 40 mW, ΔT = 20 K			
Popt = 40 mW, ΔT = Tcase - TLD			

Thermistor (Standard NTC Type)	
Doromotor	Cumbal

Parameter	Symbol	Unit	min	typ	max
Resistance	R	kΩ		10	
Beta Coefficient	β			3892	
Steinhart & Hart Coefficient A	Α		1	1.1293 x 10 ⁻³	
Steinhart & Hart Coefficient B	В		2	2.3410 x 10 ⁻⁴	
Steinhart & Hart Coefficient C	С		8	3.7755 x 10 ⁻⁸	

Measurement Conditions / Comments		
Tchip = 25° C		
$R_1/R_2 = e^{\beta}(1/T_1 - 1/T_2)$ at Tchip = 0° 50° C		
$1/T = A + B(\ln R) + C(\ln R)^3$		
T: Temperature in Kelvin		
R: resistance at T in Ω		



Revision 0.92

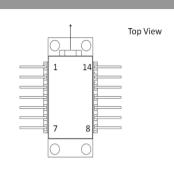
2024-05-03

SINGLE FREQUENCY LASER DFB Laser

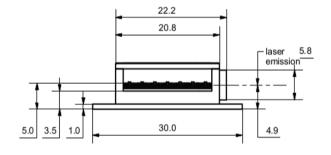


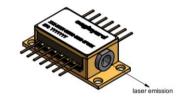
Pin Assignment

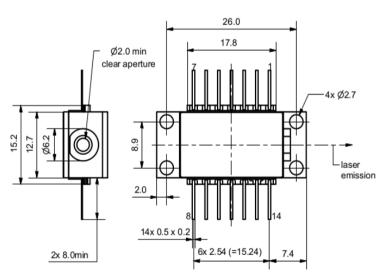
1 Thermoelectric Cooler (+)	14 Thermoelectric Cooler (-)
2 Thermistor	13 Case
3 Photo Diode Anode	12 not connected
4 Photo Diode Cathode	11 Laser Diode Cathode
5 Thermistor	10 Laser Diode Anode
6 not connected	9 not connected
7 not connected	8 not connected



Package Drawings







AIZ-20-1029-0928



Revision 0.92

2024-05-03

SINGLE FREQUENCY LASER DFB Laser



Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.



A laser diode is sensitive against optical feedback, so an optical isolator may be required in order to avoid any disturbance of the emission spectrum. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

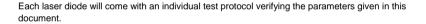


INVISIBLE LASER RADIATION

AVOID EYE OR SKIN EXPOSUR
TO DIRECT OR SCATTERED RADIATION CLASS
4 LASER PRODUCT
WAVELENGTH 795 nm
MAX. OUTPUT POWER 45 mW

IEC-60825-

Avoid direct and/or indirect exposure to the free running beam. Collimating and focussing the free running beam with optics as common in optical instruments will increase threat to the human eye.







Complies with 21 CFR 1040.10 and 1040.40

Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.